



3DK28



NPN Silicon High Frequency Low Power Switch Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation and high frequency switch, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications			Test Condition
			A	B	C	
Total Dissipation	P_{tot}	mW	300			Ta=25°C
Max. Collector Current	I_{CM}	mA	50			
Junction Temperature	T_{jm}	°C	175			
Storage Temperature	T_{stg}	°C	-55~+175			
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	35	20	20	Ic=0.1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	25	15	15	
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	4			I _E =0.1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.3			Ic=30mA I _B =3mA
Base- Emitter Saturation Voltage Drop	$V_{BE(sat)}$	V	0.9			
C-E Leakage Current	I_{CEO}	uA	0.1			V _{CE} =10V
DC Current Gain	h_{FE}		Orange: 25~40, Yellow: 40~55, Green: 55~80 Blue: 80~120, Purple: 120~180			V _{CE} =1V, Ic=300mA
Transition frequency	f_T	MHz	500			V _{CE} =10V, Ic=50mA f=100MHz
Turn-on Time	t_{on}	ns	20			Ic=30mA I _{B1} = I _{B2} =3mA
Storage Time	t_s	ns	20	15	10	
Fall Time	t_f	ns	10			

Outline and Dimensions: